KTK951S

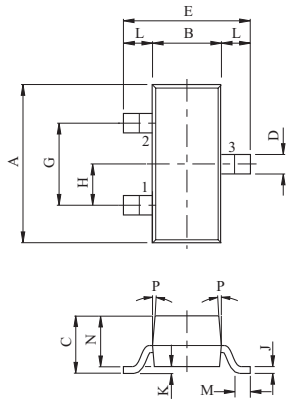
N CHANNEL JUNCTION FIELD EFFECT TRANSISTOR

LOW FREQUENCY /
HIGH FREQUENCY AMPLIFIER APPLICATION

FEATURES

· Low Gain Controlled Amplifier

· High Transter Admittance



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°

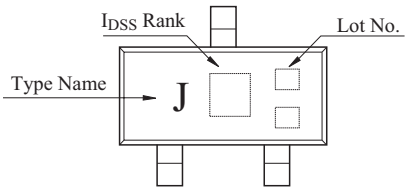
1. SOURCE
2. DRAIN
3. GATE

SOT-23

Maximum Ratings (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDO}	-22	V
Gate-Source Voltage	V_{GSO}	-22	V
Gate Current	I_G	10	mA
Drain Current	I_D	50	mA
Drain Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

Marking

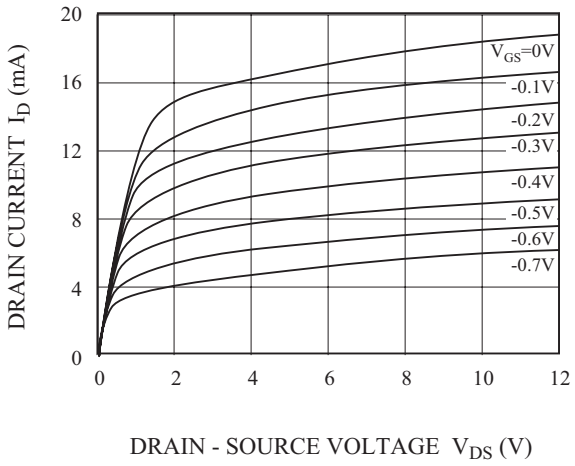


ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	V_{DS}=0V, I_G=-10μA	-22	-	-	V
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	V_{DS}=5V, I_D=10μA	0	-	-2.5	V
Gate Leakage Currnet	I_{GSS}	V_{DS}=0V, V_{GS}=-15V	-	-	10	nA
Drain Current	I_{DSS}(Note)	V_{DS}=5V, V_{GS}=0V	12	-	40	mA
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS}=5V, V_{GS}=0V, f=1kHz	20	30	-	mS
Input Capacitance	C_{iss}	V_{DS}=5V, V_{GS}=0V, f=1MHz	-	9	-	pF

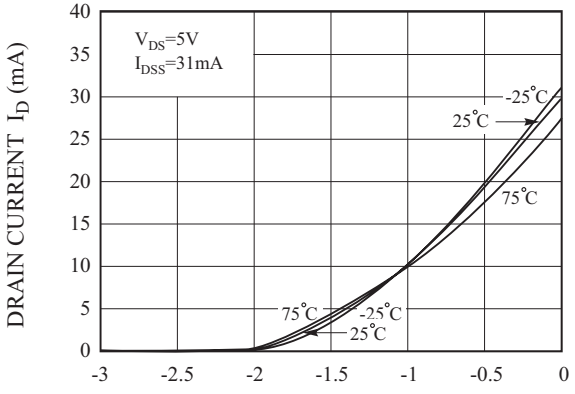
Note : I_{DSS} Classification C : 12~22, D : 18~30, E : 27~40

I_D - V_{DS}



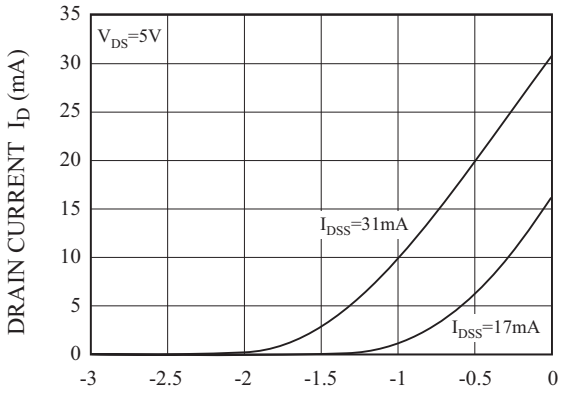
DRAIN - SOURCE VOLTAGE V_{DS} (V)

I_D - V_{GS}



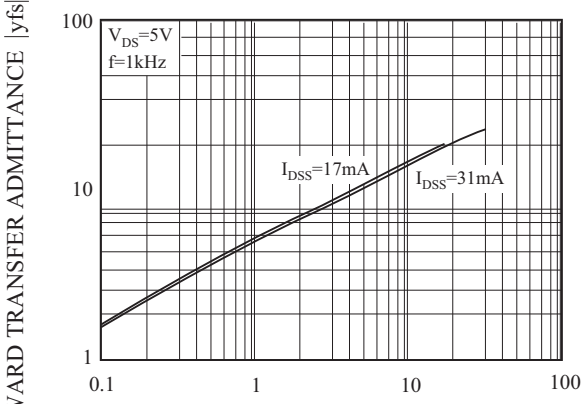
GATE - SOURCE VOLTAGE V_{GS} (V)

I_D - V_{GS}



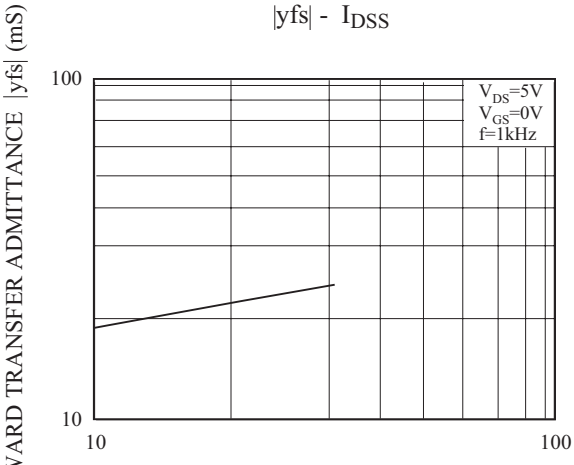
GATE - SOURCE VOLTAGE V_{GS} (V)

|yfs| - I_D



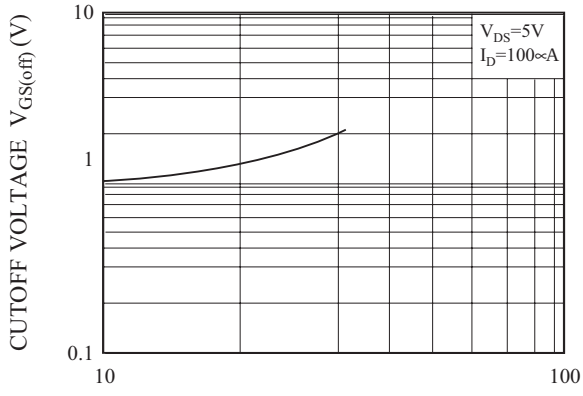
DRAIN CURRENT I_D (mA)

|yfs| - I_{DSS}



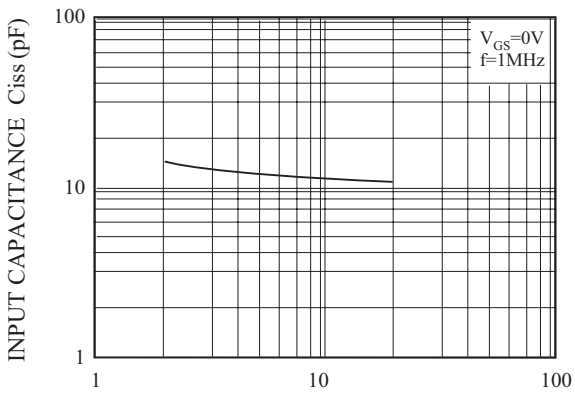
DRAIN CURRENT I_{DSS} (mA)

$V_{GS(off)}$ - I_{DSS}



DRAIN CURRENT I_{DSS} (mA)

Ciss - V_{DS}



Crss - V_{DS}